## NSN 5962-01-293-0145

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-293-0145

0.840 inches	
Body Width:	
Between 0.220 inches ar	nd 0.310 inches
Body Height:	
0.185 inches	
Maximum Power Dissip	pation Rating:
794.0 milliwatts	
Operating Tempurature	Range:
-55.0/+125.0 degrees cel	lsius
Storage Tempurature R	ange:
-65.0/+150.0 degrees cel	Isius
Features Provided:	
Schottky and programma	able and monolithic and 3-state output
Inclosure Material:	
Ceramic	
Inclosure Configuratior	1:
Dual-in-line	
Output Logic Form:	
Transistor-transistor logic	
Input Circuit Pattern:	
10 input	
Case Outline Source A	nd Designator:
D-2 mil-m-38510	
Terminal Surface Treat	ment:
Solder	
Voltage Rating And Typ	be Per Characteristic:
-0.5 volts power source	and 7.0 volts power source
Time Rating Per Chacte	eristic:
85.00 nanoseconds prop	pagation delay time, low to high level output and 85.00 nanoseconds propagation delay time, high to low level
output	
Memory Device Type:	
Prom	
Test Data Document:	
96906-mil-std-883 standa	ard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Qua	antity:
16 printed circuit	
Shelf Life:	
N/a	
Unit Of Measure:	

Yes - demil/mli

## NSN 5962-01-293-0145

Memory Microcircuit - Page 2 of 2

**Fiig:** A458a0

